

# DATA SHEET

## **BUT12; BUT12A** Silicon diffused power transistors

Product specification  
Supersedes data of February 1996  
File under Discrete Semiconductors, SC06

1997 Aug 13

# Silicon diffused power transistors

# BUT12; BUT12A

### DESCRIPTION

High-voltage, high-speed, glass-passivated NPN power transistor in a TO-220AB package.

### APPLICATIONS

- Converters
- Inverters
- Switching regulators
- Motor control systems.

### PINNING

PIN	DESCRIPTION
1	base
2	collector; connected to mounting base
3	emitter

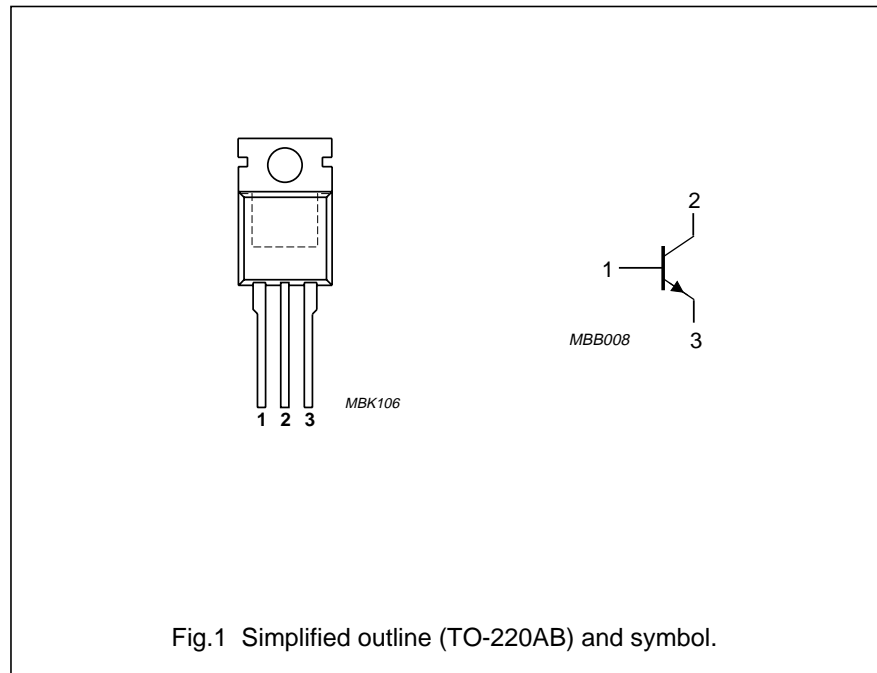


Fig.1 Simplified outline (TO-220AB) and symbol.

### QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0	850 1000	V V
	BUT12 BUT12A			
V <sub>CEO</sub>	collector-emitter voltage	open base	400 450	V V
	BUT12 BUT12A			
V <sub>CEsat</sub>	collector-emitter saturation voltage	see Fig.8	1.5	V
I <sub>Csat</sub>	collector saturation current		6 5	A A
	BUT12 BUT12A			
I <sub>C</sub>	collector current (DC)	see Figs 3 and 4	8	A
I <sub>CM</sub>	collector current (peak value)	see Fig. 4	20	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> ≤ 25 °C; see Fig.2	125	W
t <sub>f</sub>	fall time	resistive load; see Figs 12 and 13	0.8	µs

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R <sub>th j-mb</sub>	thermal resistance from junction to mounting base	1	K/W

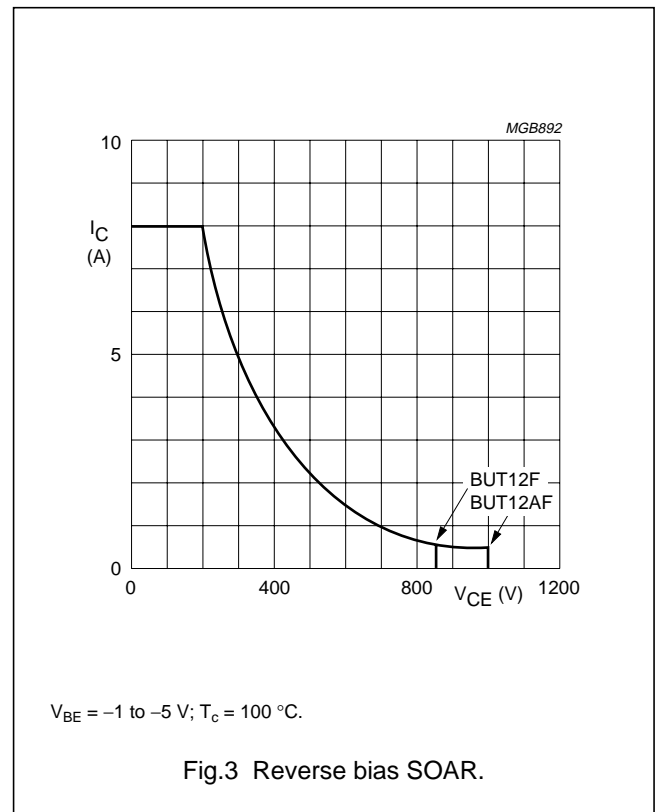
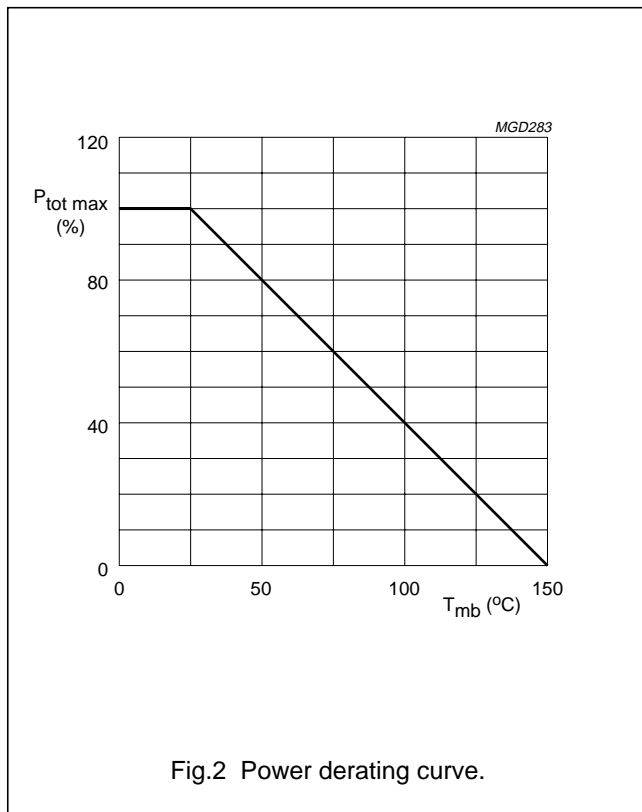
Silicon diffused power transistors

BUT12; BUT12A

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CESM}$	collector-emitter peak voltage	$V_{BE} = 0$			
	BUT12		–	850	V
	BUT12A	–	1000	V	
$V_{CEO}$	collector-emitter voltage	open base			
	BUT12		–	400	V
	BUT12A	–	450	V	
$I_{Csat}$	collector saturation current				
	BUT12	–	6	A	
	BUT12A	–	5	A	
$I_C$	collector current (DC)	see Figs 3 and 4	–	8	A
$I_{CM}$	collector current (peak value)	see Fig. 4	–	20	A
$I_B$	base current (DC)		–	4	A
$I_{BM}$	base current (peak value)		–	6	A
$P_{tot}$	total power dissipation	$T_{mb} \leq 25\text{ }^\circ\text{C}$ ; see Fig.2	–	125	W
$T_{stg}$	storage temperature		–65	+150	$^\circ\text{C}$
$T_j$	junction temperature		–	150	$^\circ\text{C}$



## Silicon diffused power transistors

## BUT12; BUT12A

## CHARACTERISTICS

$T_j = 25\text{ °C}$  unless otherwise specified.

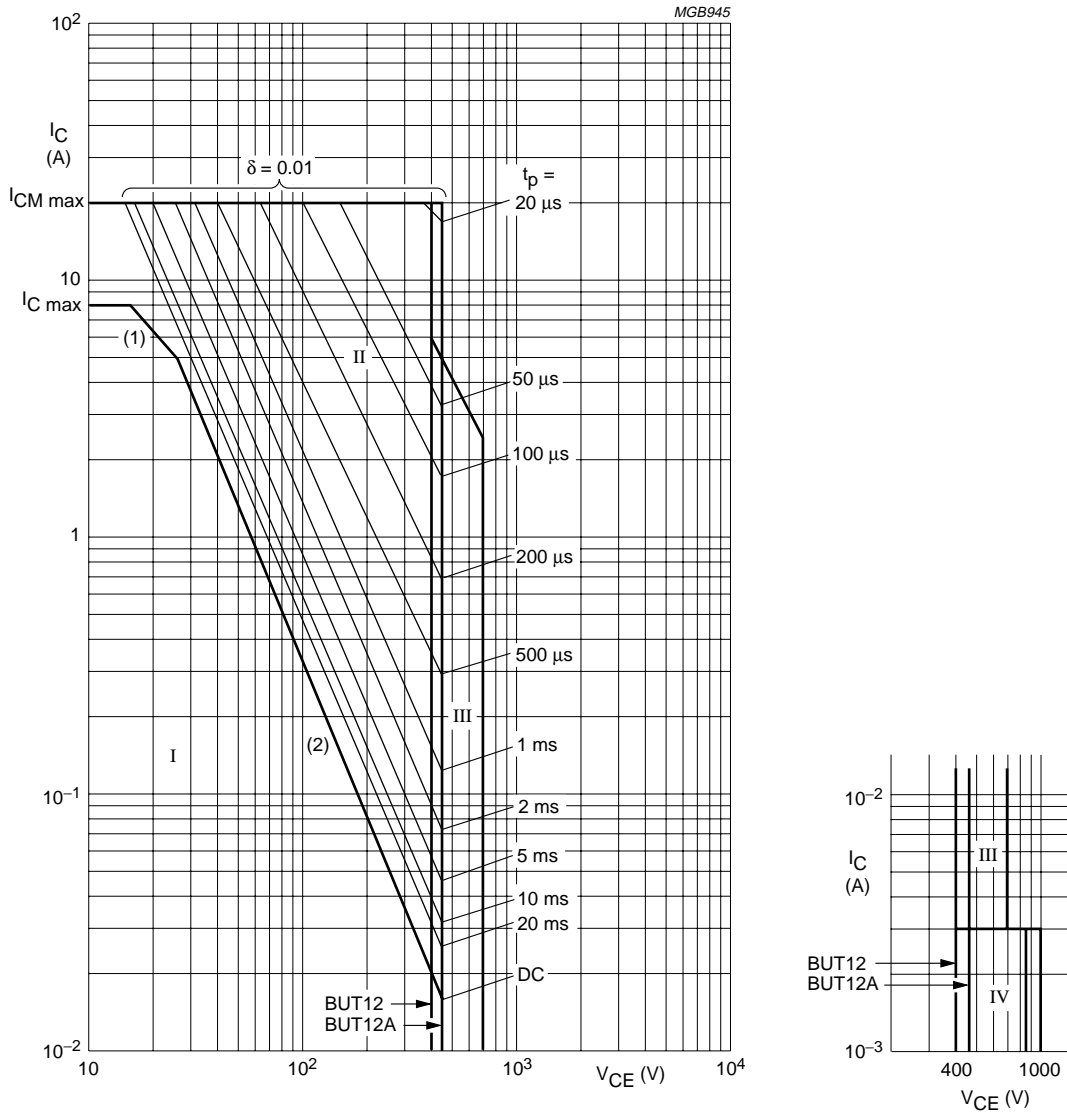
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{CEOsust}$	collector-emitter sustaining voltage BUT12 BUT12A	$I_C = 100\text{ mA}$ ; $I_{Boff} = 0$ ; $L = 25\text{ mH}$ ; see Figs 6 and 7	400	–	–	V
			450	–	–	V
$V_{CEsat}$	collector-emitter saturation voltage BUT12 BUT12A	$I_C = 6\text{ A}$ ; $I_B = 1.2\text{ A}$ ; see Figs 8 and 10	–	–	1.5	V
		$I_C = 5\text{ A}$ ; $I_B = 1\text{ A}$ ; see Figs 8 and 10	–	–	1.5	V
$V_{BEsat}$	base-emitter saturation voltage BUT12 BUT12A	$I_C = 6\text{ A}$ ; $I_B = 1.2\text{ A}$ ; see Fig.8	–	–	1.5	V
		$I_C = 5\text{ A}$ ; $I_B = 1\text{ A}$ ; see Fig.8	–	–	1.5	V
$I_{CES}$	collector-emitter cut-off current	$V_{CE} = V_{CESmax}$ ; $V_{BE} = 0$ ; note 1	–	–	1	mA
		$V_{CE} = V_{CESmax}$ ; $V_{BE} = 0$ ; $T_j = 125\text{ °C}$ ; note 1	–	–	3	mA
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = 9\text{ V}$ ; $I_C = 0$	–	–	10	mA
$h_{FE}$	DC current gain	$V_{CE} = 5\text{ V}$ ; $I_C = 10\text{ mA}$ ; see Fig.11	10	18	35	
		$V_{CE} = 5\text{ V}$ ; $I_C = 1\text{ A}$ ; see Fig.11	10	20	35	
<b>Switching times resistive load</b> (see Figs 12 and 13)						
$t_{on}$	turn-on time BUT12 BUT12A	$I_{Con} = 6\text{ A}$ ; $I_{Bon} = -I_{Boff} = 1.2\text{ A}$	–	–	1	$\mu\text{s}$
		$I_{Con} = 5\text{ A}$ ; $I_{Bon} = -I_{Boff} = 1\text{ A}$	–	–	1	$\mu\text{s}$
$t_s$	storage time BUT12 BUT12A	$I_{Con} = 6\text{ A}$ ; $I_{Bon} = -I_{Boff} = 1.2\text{ A}$	–	–	4	$\mu\text{s}$
		$I_{Con} = 5\text{ A}$ ; $I_{Bon} = -I_{Boff} = 1\text{ A}$	–	–	4	$\mu\text{s}$
$t_f$	fall time BUT12 BUT12A	$I_{Con} = 6\text{ A}$ ; $I_{Bon} = -I_{Boff} = 1.2\text{ A}$	–	–	0.8	$\mu\text{s}$
		$I_{Con} = 5\text{ A}$ ; $I_{Bon} = -I_{Boff} = 1\text{ A}$	–	–	0.8	$\mu\text{s}$
<b>Switching times inductive load</b> (see Figs 14 and 15)						
$t_s$	storage time BUT12 BUT12A	$I_{Con} = 6\text{ A}$ ; $I_{Bon} = 1.2\text{ A}$ ; $V_{CL} = 250\text{ V}$ ; $T_c = 100\text{ °C}$	–	1.9	2.5	$\mu\text{s}$
		$I_{Con} = 5\text{ A}$ ; $I_{Bon} = 1\text{ A}$ ; $V_{CL} = 300\text{ V}$ ; $T_c = 100\text{ °C}$	–	1.9	2.5	$\mu\text{s}$
$t_f$	fall time BUT12 BUT12A	$I_{Con} = 6\text{ A}$ ; $I_{Bon} = 1.2\text{ A}$ ; $V_{CL} = 250\text{ V}$ ; $T_c = 100\text{ °C}$	–	200	300	ns
		$I_{Con} = 5\text{ A}$ ; $I_{Bon} = 1\text{ A}$ ; $V_{CL} = 300\text{ V}$ ; $T_c = 100\text{ °C}$	–	200	300	ns

## Note

1. Measured with a half-sinewave voltage (curve tracer).

Silicon diffused power transistors

BUT12; BUT12A



$T_{mb} < 25\ ^\circ C$ .

I - Region of permissible DC operation.

II - Permissible extension for repetitive pulse operation.

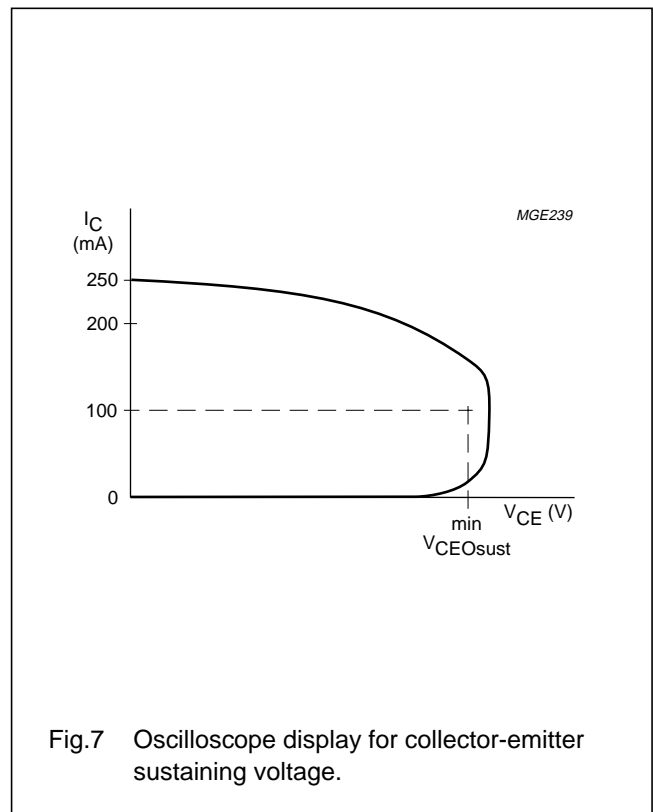
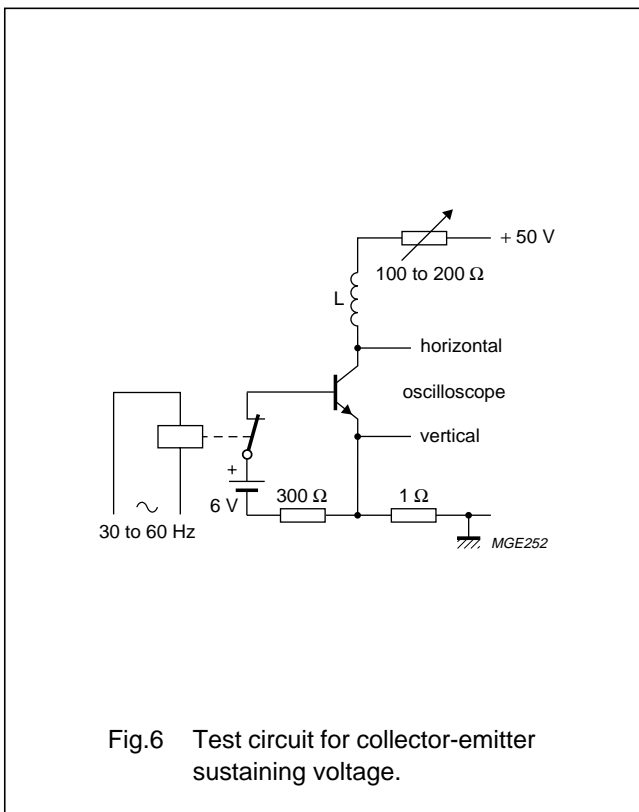
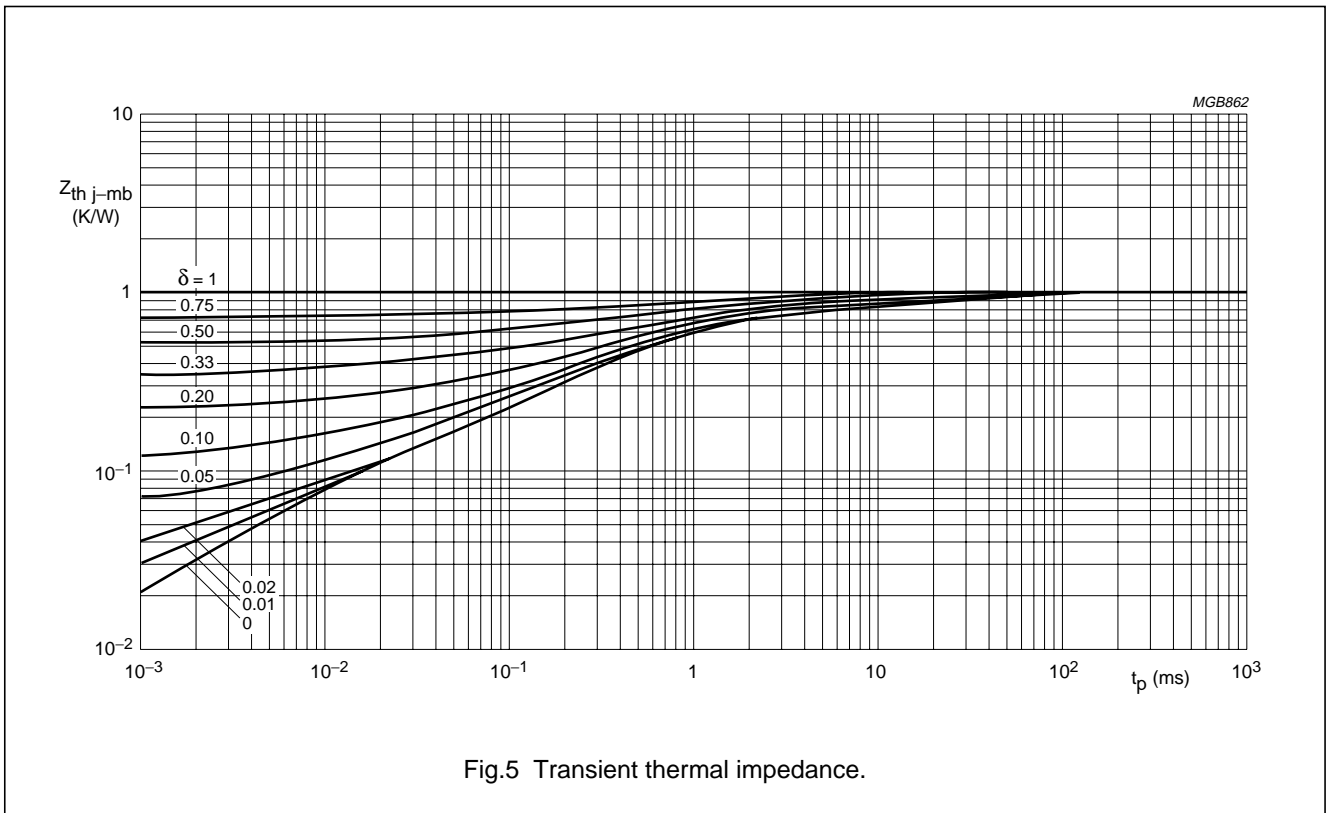
(1)  $P_{tot\ max}$  and  $P_{tot\ peak\ max}$  lines.

(2) Second breakdown limits.

Fig.4 Forward bias SOAR.

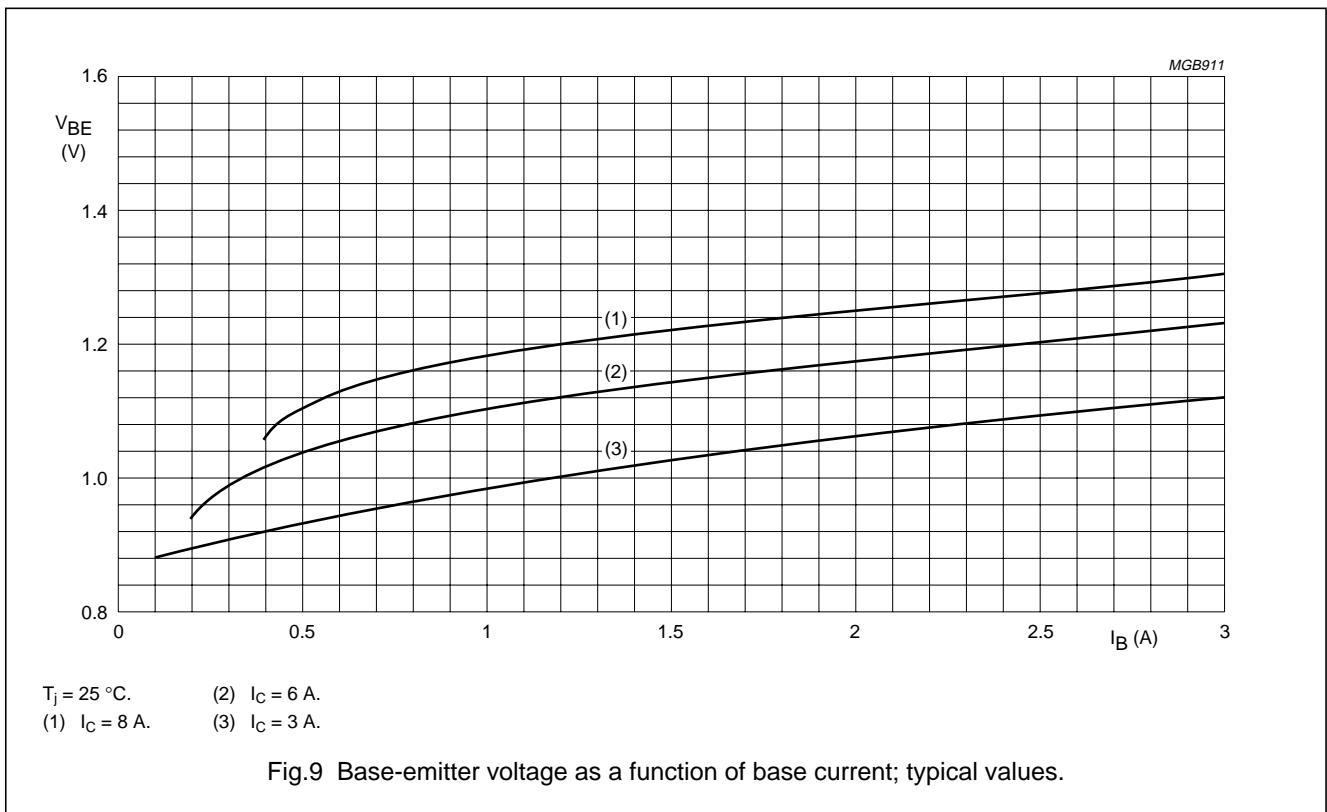
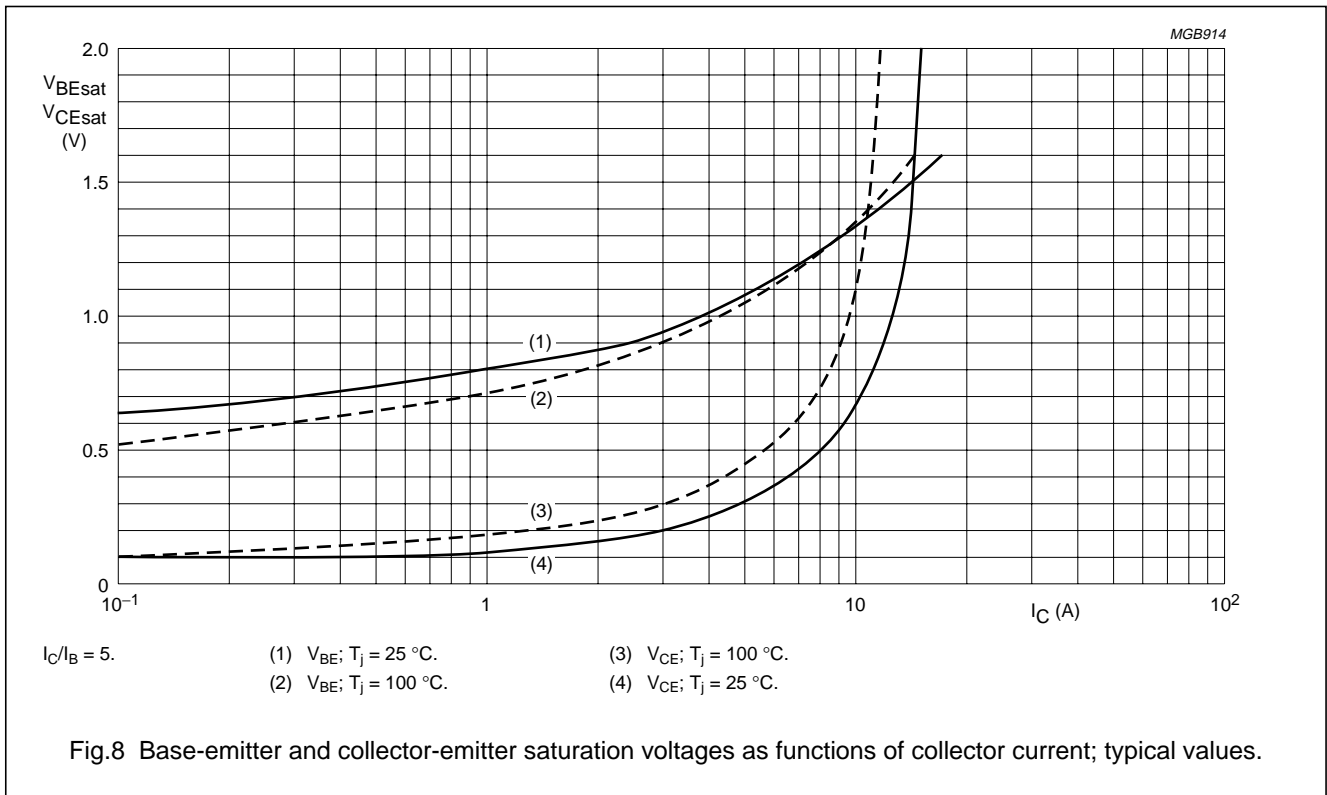
Silicon diffused power transistors

BUT12; BUT12A



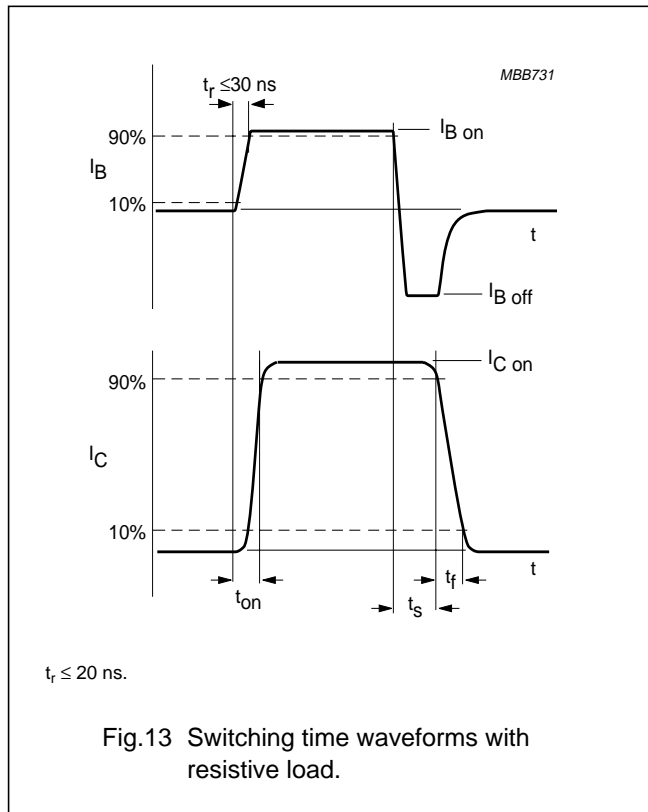
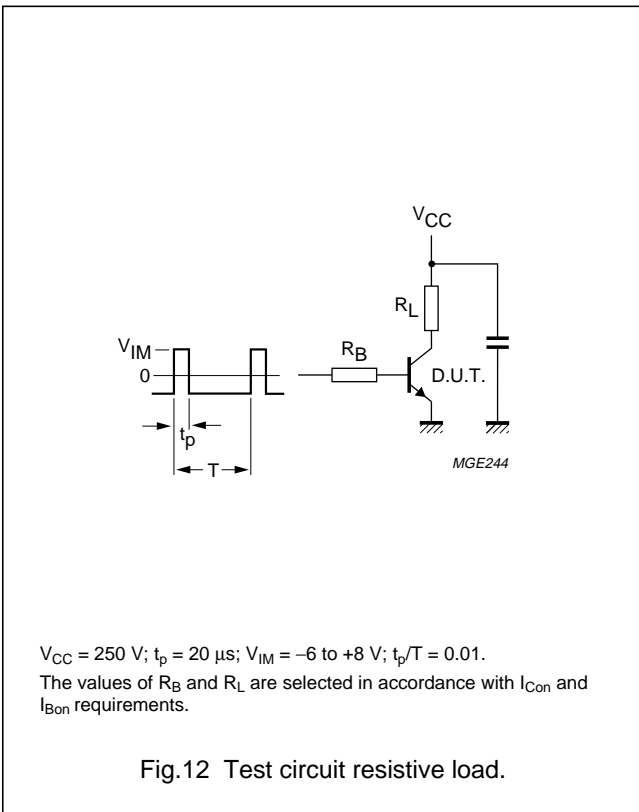
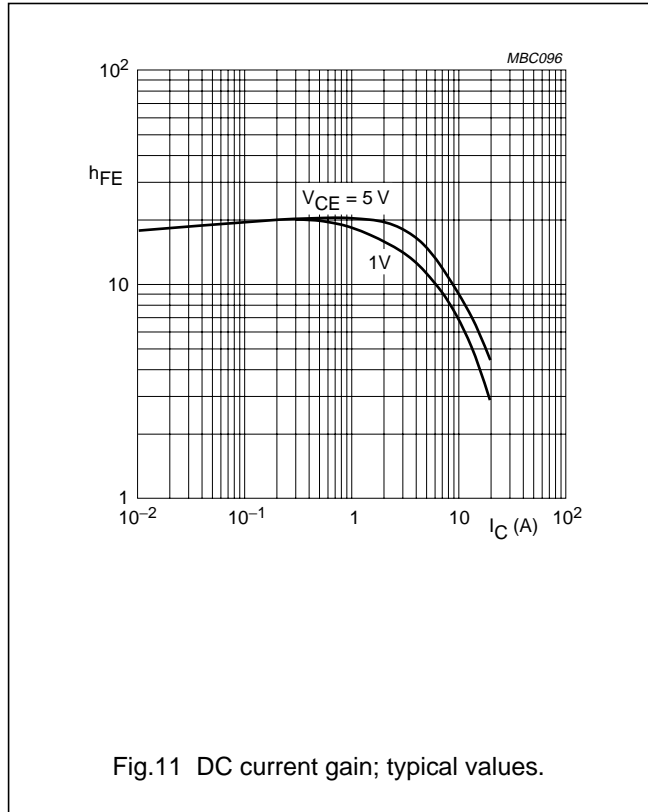
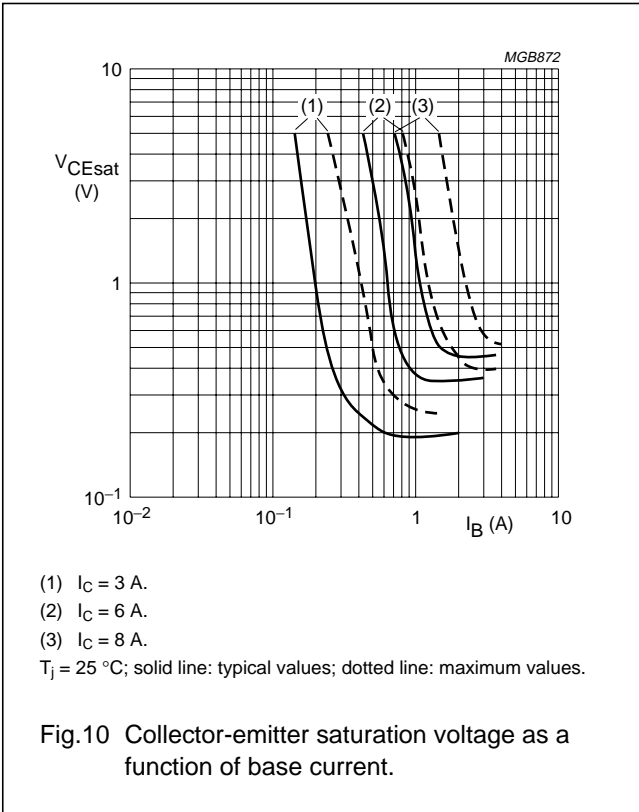
Silicon diffused power transistors

BUT12; BUT12A



Silicon diffused power transistors

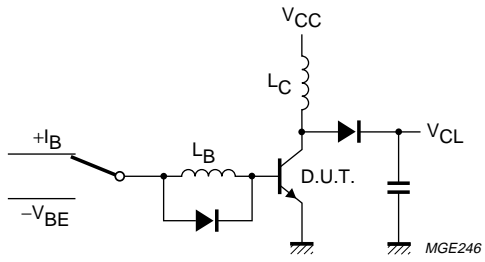
BUT12; BUT12A





Silicon diffused power transistors

BUT12; BUT12A



$V_{CL}$  = up to 1000 V;  $V_{CC}$  = 30 V;  $V_{BE}$  = -1 to -5 V;  $L_B$  = 1  $\mu$ H;  
 $L_C$  = 200  $\mu$ H.

Fig.14 Test circuit inductive load and reverse bias SOAR.

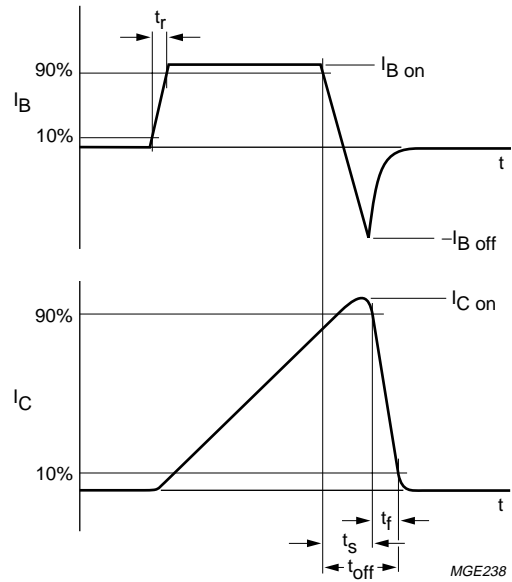


Fig.15 Switching time waveforms with inductive load.

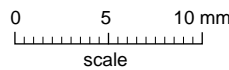
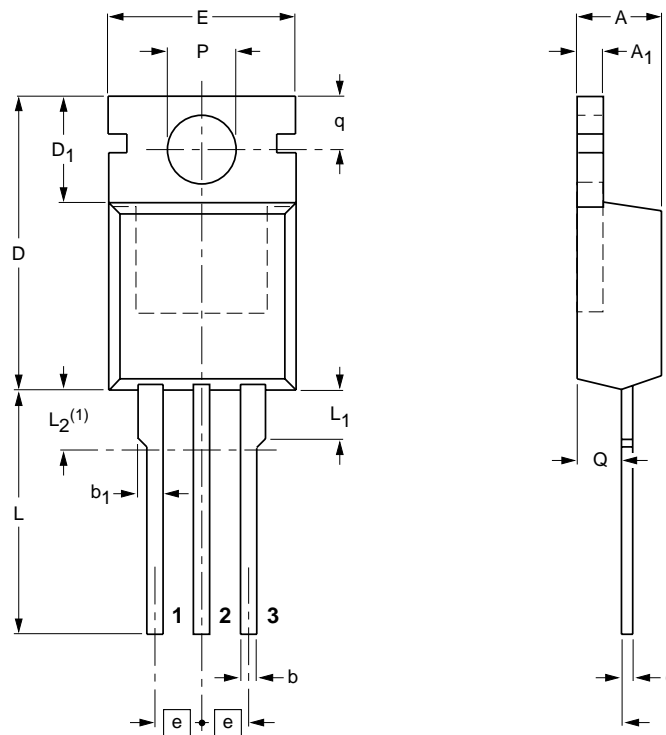
Silicon diffused power transistors

BUT12; BUT12A

PACKAGE OUTLINE

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220

SOT78



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b	b <sub>1</sub>	c	D	D <sub>1</sub>	E	e	L	L <sub>1</sub>	L <sub>2</sub> <sup>(1)</sup> max.	P	q	Q
mm	4.5 4.1	1.39 1.27	0.9 0.7	1.3 1.0	0.7 0.4	15.8 15.2	6.4 5.9	10.3 9.7	2.54	15.0 13.5	3.30 2.79	3.0	3.8 3.6	3.0 2.7	2.6 2.2

Note

1. Terminals in this zone are not tinned.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT78		TO-220				97-06-11

## Silicon diffused power transistors

## BUT12; BUT12A

**DEFINITIONS**

<b>Data sheet status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
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